

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|---|---|------------------|
| 1 | 14585 | (silicon same (etch\$3 or pattern\$3)) same (reactive near ion near etch\$3 or "RIE") | USPAT, US-PGPUB; EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 17:11 |
| 2 | 2867 | ((silicon same (etch\$3 or pattern\$3)) same (reactive near ion near etch\$3 or "RIE")) same trench | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 14:22 |
| 3 | 773 | ((silicon same (etch\$3 or pattern\$3)) same (reactive near ion near etch\$3 or "RIE")) same trench) same insulat\$3 | USPAT, US-PGPUB; EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 14:25 |
| 4 | 9 | ((silicon same (etch\$3 or pattern\$3)) same (reactive near ion near etch\$3 or "RIE")) same trench) same insulat\$3) and ((fill\$3 same trench) near5 silicon) | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 17:02 |
| 5 | 93 | (silicon same (etch\$3 or pattern\$3)) and ((fill\$3 same trench) near5 silicon) | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 16 40 |
| 6 | 66 | ((silicon same (etch\$3 or pattern\$3)) and ((fill\$3 same trench) near5 silicon)) and @pd<20011226 | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 16 42 |
| 7 | 55 | (silicon same (etch\$3 or pattern\$3)) same ((fill\$3 same trench) near5 silicon) | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 16 41 |
| 8 | 42 | ((silicon same (etch\$3 or pattern\$3)) same ((fill\$3 same trench) near5 silicon)) and @pd<20011226 | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 16 48 |
| 9 | 31 | ((silicon same (etch\$3 or pattern\$3)) same ((fill\$3 same trench) near5 silicon)) and @pd<20011226) and (reactive near ion near etch\$3 or "RIE") | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 16 48 |
| 10 | 41 | ((silicon same (etch\$3 or pattern\$3)) same (reactive near ion near etch\$3 or "RIE")) and ((fill\$3 same trench) near5 silicon) | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 17:31 |
| 11 | 35 | ((silicon same (etch\$3 or pattern\$3)) same (reactive near ion near etch\$3 or "RIE")) and ((fill\$3 same trench) near5 silicon)) and @pd<20011226 | USPAT, US-PGPUB, EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 17:04 |
| 12 | 141 | ((silicon same (etch\$3 or pattern\$3)) same (reactive near ion near etch\$3 or "RIE")) and 438/719.ccls. | USPAT, US-PGPUB; EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 17:12 |
| 13 | 1703 | 438/706,719.ccls. ((fill\$3 same trench) near5 silicon) | USPAT, US-PGPUB; EPO, JPO; DERWENT, IBM_TDB | 2003/05/20 17:32 |

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|----|--------|--|---|------------------|
| 14 | 1 | 438/706,719.ccls. and ((fill\$3 same trench) near5 silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 33 |
| 15 | 0 | lee-byeung-leul.in. and ((fill\$3 same trench) near5 silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 37 |
| 16 | 7 | lee-byeung-leul.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 34 |
| 17 | 0 | 216/39,66, 79.ccls. and ((fill\$3 same trench) near5 silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 38 |
| 18 | 293527 | 216/ 79.ccls. and ((fill\$3 same trench) near5 silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 41 |
| 19 | 5026 | (216/ 79.ccls. and ((fill\$3 same trench) near5 silicon)) and (reactive near ion near etch\$3 or "RIE") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 39 |
| 20 | 3450 | ((216/ 79.ccls. and ((fill\$3 same trench) near5 silicon)) and (reactive near ion near etch\$3 or "RIE")) and ((etch\$3 or pattern\$3) same silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 40 |
| 21 | 55 | ((pattern\$3 or etch\$3) same silicon) same ((fill\$3 same trench) near5 silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 41 |
| 22 | 37 | ((pattern\$3 or etch\$3) same silicon) same ((fill\$3 same trench) near5 silicon)) and @pd<20010312 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/20 17 42 |